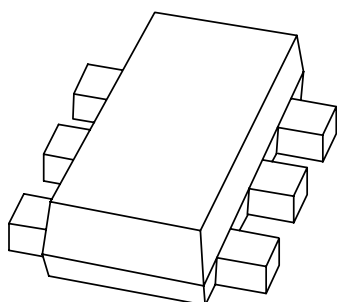


DATA SHEET



PEMB10

PNP resistor-equipped double
transistor $R1 = 2.2 \text{ k}\Omega$, $R2 = 47 \text{ k}\Omega$

Preliminary specification

2001 Sep 14

PNP resistor-equipped double transistor
R1 = 2.2 kΩ, R2 = 47 kΩ

PEMB10

FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm × 1.2 mm × 0.55 mm ultra thin package
- Excellent coplanarity due to straight leads
- Reduces number of components as replacement of two SC-75/SC-89 packaged transistors
- Reduces required board space
- Reduces pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

DESCRIPTION

PNP resistor-equipped double transistor in a SOT666 plastic package.

MARKING

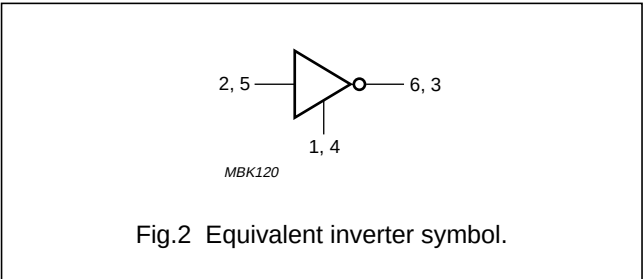
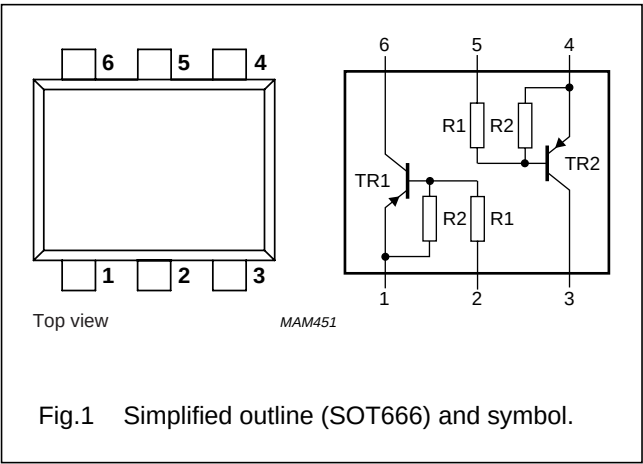
TYPE NUMBER	MARKING CODE
PEMB10	Z5

PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	−50	V
I _{CM}	peak collector current	−100	mA
TR1	PNP	−	−
TR2	PNP	−	−
R1	bias resistor	2.2	kΩ
R2	bias resistor	47	kΩ



PNP resistor-equipped double transistor

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PEMB10

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor					
V _{CBO}	collector-base voltage	open emitter	–	–50	V
V _{CEO}	collector-emitter voltage	open base	–	–50	V
V _{EBO}	emitter-base voltage	open collector	–	–10	V
V _I	input voltage				
	positive		–	+12	V
	negative		–	–5	V
I _O	output current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	300	mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

1. Transistor mounted on an FR4 printed-circuit board.
2. The only recommended soldering method is reflow soldering.

PNP resistor-equipped double transistor

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PEMB10

CHARACTERISTICS $T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor						
I_{CBO}	collector cut-off current	$I_{\text{E}} = 0$; $V_{\text{CB}} = -50 \text{ V}$	–	–	–100	nA
I_{CEO}	collector cut-off current	$I_{\text{B}} = 0$; $V_{\text{CE}} = -50 \text{ V}$	–	–	–1	μA
		$I_{\text{B}} = 0$; $V_{\text{CE}} = -30 \text{ V}$; $T_{\text{j}} = 150 \text{ }^{\circ}\text{C}$	–	–	–50	μA
I_{EBO}	emitter cut-off current	$I_{\text{C}} = 0$; $V_{\text{EB}} = -5 \text{ V}$	–	–	–180	μA
h_{FE}	DC current gain	$I_{\text{C}} = -10 \text{ mA}$; $V_{\text{CE}} = -5 \text{ V}$	100	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_{\text{C}} = -5 \text{ mA}$; $I_{\text{B}} = -0.25 \text{ mA}$	–	–	–100	mV
$V_{\text{i(off)}}$	input-off voltage	$I_{\text{C}} = -100 \text{ }\mu\text{A}$; $V_{\text{CE}} = -5 \text{ V}$	–	–0.6	–0.5	V
$V_{\text{i(on)}}$	input-on voltage	$I_{\text{C}} = -5 \text{ mA}$; $V_{\text{CE}} = -0.3 \text{ V}$	–1.1	–0.75	–	V
$R1$	input resistor		1.54	2.2	2.86	$\text{k}\Omega$
$\frac{R2}{R1}$	resistor ratio		17	21	26	
C_{c}	collector capacitance	$I_{\text{E}} = i_{\text{e}} = 0$; $V_{\text{CB}} = -10 \text{ V}$; $f = 1 \text{ MHz}$	–	–	3	pF

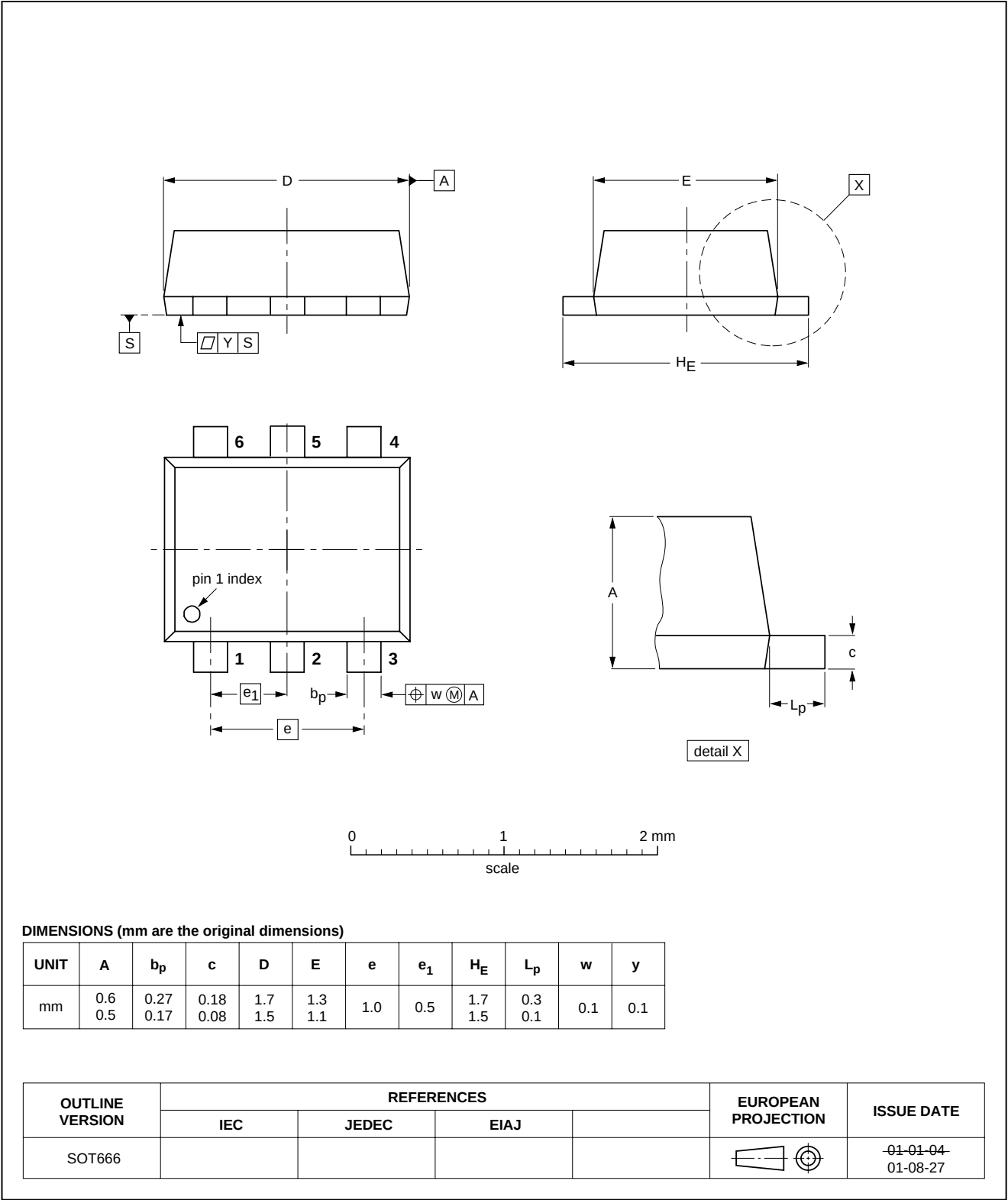
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



PNP resistor-equipped double transistor

R1 = 2.2 k Ω , R2 = 47 k Ω

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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NOTES

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